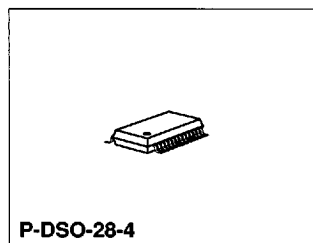


Preliminary Data

Bipolar IC

Features

- Heterodyne receiver with demodulator
- Down mixing from 900 MHz receiver band to the base band
- Demodulation and generation of I/Q-baseband components
- Low mixer noise 10 dB (SSB)
- Input high intercept point + 2 dB
- Integrated 0° and 90° phase shifter
- 82 dB AGC-range
- On-chip second LO-oscillator with external tuning circuit
- Two differential operational amplifiers
- Low power consumption due to highly flexible power-down capability
- Wide input frequency range up to 1 GHz
- Wide IF-range from 35 MHz to 100 MHz
- Wide output frequency range up to 13.5 MHz
- P-DSO-28-4 shrink package
- Temperature range – 25 °C to 85 °C



Applications

- Digital mobile cellular systems as GSM, DAMPS, JDC
- Various demodulation schemes, such as PM, PSK, FSK, QAM, QPSK, GMSK
- Space and power saving optimizations of existing discrete demodulator circuits

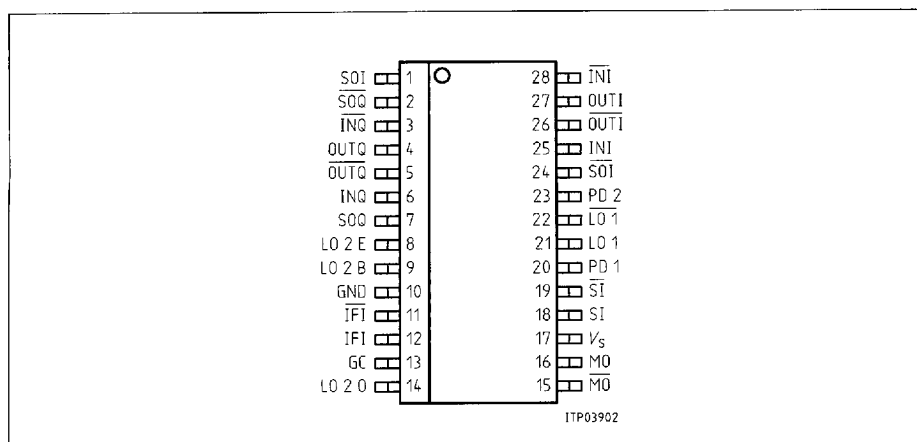
Type	Version	Ordering Code	Package
PMB 2402S	V 2.1	Q67000-A6072	P-DSO-28-4 (Shrink, SMD))
PMB 2402S	V 2.1	Q67006-A6072	P-DSO-28-4 (Shrink, SMD, Tape + Reel)

Functional Description

The PMB 2402 is a single-chip single-conversion heterodyn PM-receiver with phase shifting circuitry for the I/Q-phase baseband demodulation on chip. It also includes the second local oscillator, a gain controlled second IF-amplifier, two differential operational amplifiers for baseband filtering purposes and power down circuitry.

The PMB 2402 is designed for digital mobile telephones according to the GSM-standard and other digital systems.

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Pin Configuration
(top view)

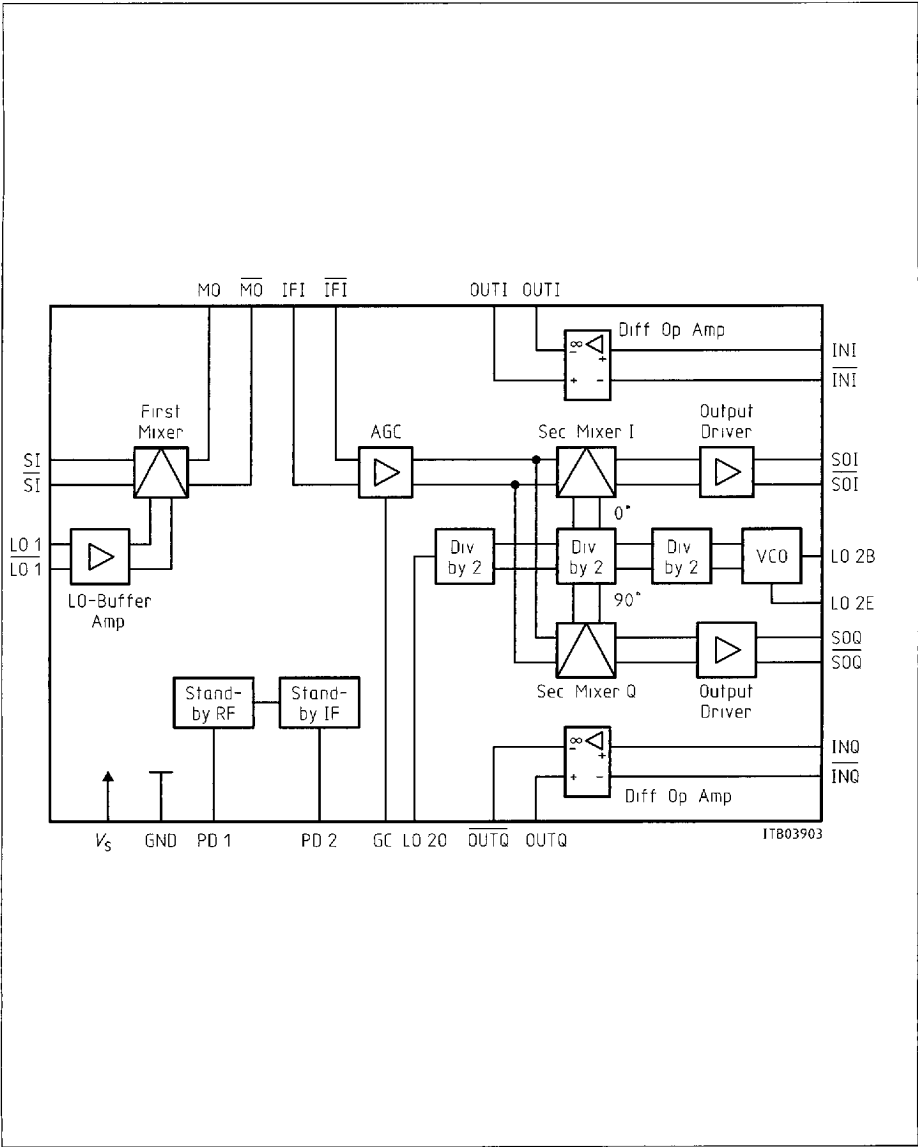
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Pin Definitions and Functions

Pin No.	Symbol	Function
1	SOI	Non-inverting in-phase signal output
2	SOQ	Non-inverting quadratur signal output
3	$\overline{\text{INQ}}$	Inverting op. amp. signal output (Q)
4	OUTQ	Non-inverting op. amp. signal output (Q)
5	$\overline{\text{OUTQ}}$	Inverting op. amp. signal output (Q)
6	INQ	Non-inverting op. amp. signal input (Q)
7	SOQ	Inverting quadratur signal output
8	LO2E	External capacitors for oscillator
9	LO2B	VCO-tuning circuit
10	GND	Ground
11	$\overline{\text{IFI}}$	Inverting IF input
12	IFI	Non-inverting IF input
13	GC	Gain control input
14	LO2O	VCO-signal output
15	$\overline{\text{MO}}$	Inverted output of first mixer
16	MO	Non-inverted output of first mixer
17	V_s	Supply voltage
18	SI	Non-inverted signal input of first mixer
19	$\overline{\text{SI}}$	Inverted signal input of first mixer
20	PD1	Power-down input 1
21	LO1	Non-inverting input for first local oscillator
22	$\overline{\text{LO1}}$	Inverting input for first local oscillator
23	PD2	Power-down input 2
24	$\overline{\text{SOI}}$	Inverting in-phase signal output
25	INI	Non-inverting op. amp. signal input (I)
26	$\overline{\text{OUTI}}$	Inverting op. amp. signal output (I)
27	OUTI	Non-inverting op. amp. signal output (I)
28	$\overline{\text{INI}}$	Inverting op. amp. signal input (I)



Block Diagram

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Circuit Description

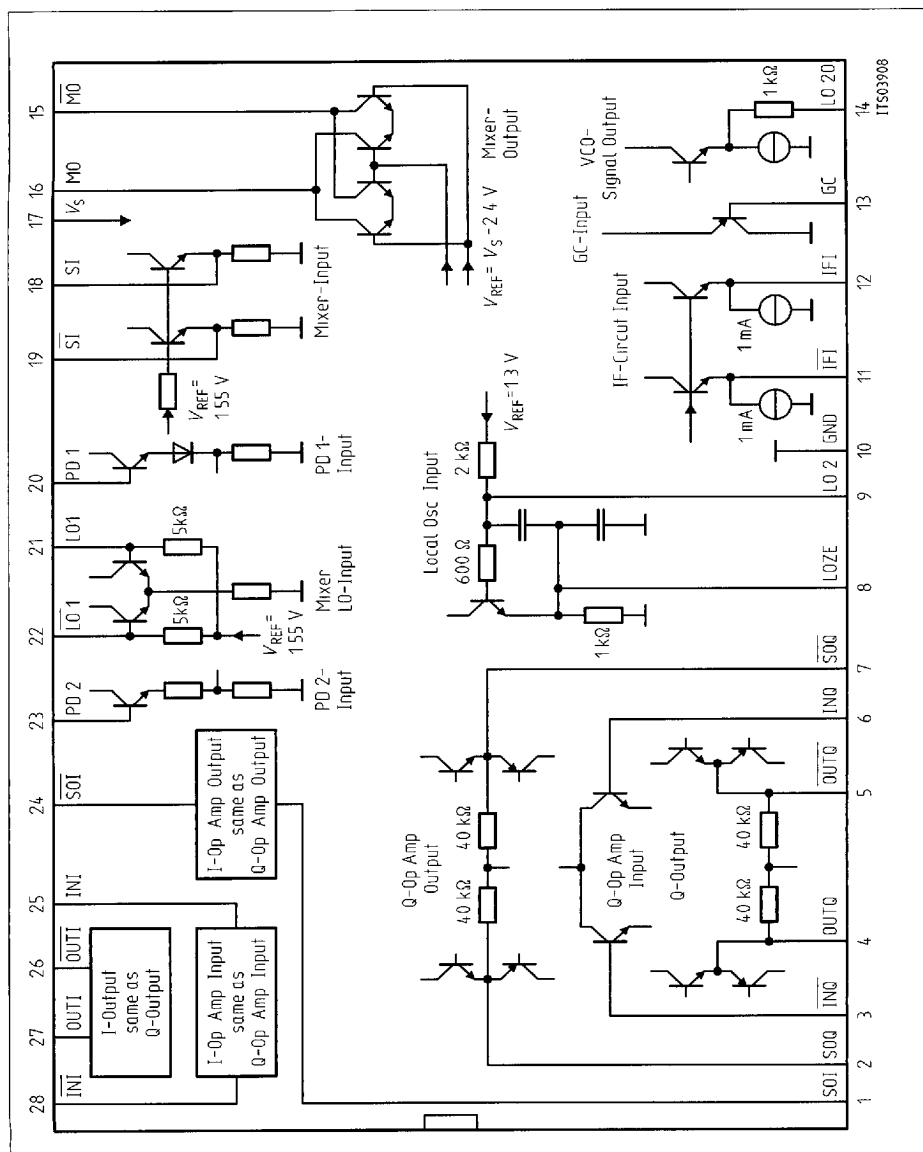
The input signal $SI/\overline{SI}$ and the amplified first local oscillator signal $LO1/\overline{LO1}$ are mixed down to an intermediate frequency (IF). The open collector output of the mixer generates a differential current at pins $MO/\overline{MO}$ which is filtered by an external resonant circuit. The resulting voltage drives an external SAW-filter.

The second local oscillator signal $LO2$ is generated in an on chip VCO and is fed to two dividers, which generate orthogonal signals at a quarter of VCO-frequency. The internal LO-signal is fed to an additionally divider, whose output signal $LO2O$ is fed to the RF-signal of PLL-synthesizer. The filtered IF-signal reenters the chip at the $IFI/\overline{FI}$ input, where it is amplified and demodulated to the final baseband output frequency with each of the orthogonal signals. The resulting in-phase and quadrature signals pass through differential output drivers and appear at $SOI/\overline{SOI}$ and $SOQ/\overline{SOQ}$ outputs, respectively. The amplification of the IF-signal before the second mixer stage is performed by a gain-controlled amplifier, the gain being determined by the voltage at the gain control input GC .

Two differential operational amplifiers with the input signals $INI/\overline{INI}$ ($INQ/\overline{INQ}$) and the output signals $OUTI/\overline{OUTI}$ ($OUTQ/\overline{OUTQ}$) can be used as active filters.

Differential signals and symmetrical circuitry are used throughout, except at the signal output. Bias drivers generate internal temperature- and supply voltage-compensated reference voltages required by various circuit blocks. Switching the power down inputs $PD1$ and $PD2$ from high to low (see table) sets the circuit from its normal operating mode into a mode with reduced supply current.

PD1	PD2	RF-Part	IF-Part	VCO/Divders
L	L	OFF	OFF	ON
L	H	OFF	ON	ON
H	L	ON	OFF	ON
H	H	ON	ON	ON



Internal Input / Output Circuits

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Electrical Characteristics

Absolute Maximum Ratings

The maximum ratings may not be exceeded under any circumstances, not even momentarily and individually, as permanent damage to the IC will result.

$T_A = -25\text{ }^{\circ}\text{C}$ to $85\text{ }^{\circ}\text{C}$

Parameter	Symbol	Limit Values		Unit	Remarks
		min.	max.		
Supply voltage	V_S	-0.5	7	V	
Input/output voltage (any except open collector)	V_{IO}	-0.5 -0.5	$V_S + 0.5$ 7.5	V V	$V_S \leq 7\text{ V}$ $V_S \leq 7\text{ V}$
Open collector output voltage (MO/MO)	V_{OC}	-0.5 -0.5	$V_S + 2.5$ 7.5	V V	$V_S \geq 5\text{ V}$ $V_S \geq 5\text{ V}$
Differential input voltage (any differential input)	V_I	-3	3	V	
Junction temperature	T_J		125	$^{\circ}\text{C}$	
Storage temperature	T_{stg}	-55	125	$^{\circ}\text{C}$	
Thermal resistance (junction to ambient)	$R_{th JA}$		55	K/W K/W	PDSO-28 P-DSO-28-S

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Operational Range

Within the operational range the IC operates as described in the circuit description. The AC/DC-characteristics limits are not guaranteed.

$V_S = 4.5 \text{ V to } 5.5 \text{ V}$; $T_A = -25 \text{ }^\circ\text{C to } 85 \text{ }^\circ\text{C}$; refer to test circuit 1.

Parameter	Symbol	Limit Values		Unit	Remarks
		min.	max.		
SI/ $\overline{\text{SI}}$ input level	P_{SI}		- 11	dBm	
SI/ $\overline{\text{SI}}$ input frequency	f_{SI}		1000	MHz	
LO1/ $\overline{\text{LO1}}$ input level	P_{LO1}	- 11	3	dBm	
LO1/ $\overline{\text{LO1}}$ input frequency	f_{LO1}		1100	MHz	
Intermediate frequency	f_{IF}	35	100	MHz	
IF1/ $\overline{\text{IF1}}$ input level	P_{IF1}		- 24	dBm	
IF1/ $\overline{\text{IF1}}$ input frequency	f_{IF1}	35	100	MHz	
LO2 input level	P_{LO2}	- 20	0	dBm	VCO external
LO2 input frequency	f_{LO2}	140	400	MHz	
VCO frequency range	f_{VCO}	120	250	MHz	with ext. capacitors
LO2O output level	P_{LO2O}	120	180	mVpp	
LO2O output frequency	f_{LO2O}	15	50	MHz	
SOI/ $\overline{\text{SOI}}$, SOQ/ $\overline{\text{SOQ}}$ output Bandwidth	B_{SO}	0	13.5	MHz	- 3 dB roll off
GC input voltage	V_{GC}	0	2	V	
L-PD1/PD2 voltage	V_{PDL}	0	1	V	
H-PD1/PD2 voltage	V_{PDH}	4	V_S	V	

Note: Power levels are referred to resistance of 50 Ω

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AC/DC Characteristics

AC/DC-characteristics involve the spread of values guaranteed within the specified supply voltage and ambient temperature range. Typical characteristics are the median of the production.

$V_S = 4.75$ to 5.25 V; $T_A = 25$ °C;

Parameter	Symbol	Limit Values			Unit	Test Condition	Test Circuit
		min.	typ.	max.			
Supply current	I_S	3.1	5.5	6.8	mA	PD1 = L PD2 = L	1
		12	15.5	19	mA	PD1 = L PD2 = H	
		11.5	15	18.5	mA	PD1 = H PD2 = L	
		20	24.5	30	mA	PD1 = H PD2 = L	

First Mixer Signal Input SI/ $\bar{S}$ I

Input resistance	R_{SI}	17	25	33	Ω		2a
Input inductance	L_{SI}	3.5	5	6.5	nH	In series to R_{SI}	2a
Max. input level	P_{SI}	-13	-11		dBm	1 dB compr. at MO/ $\bar{M}$ O	1
Input intercept Point	P_{IPI}	0	2	3	dBm	$G_{MO} = 14$ dB	1
Blocking level	P_B	-16	-14	-12	dBm	3 dB attenuation of wanted Signal at MO	1
Input interference level at $f = f_{int}$	P_{int}	-38			dBm	-98 dBm interference at $f = (f_{int} \pm f_{LO1}) \times 2$ at MO	3
Input frequency	f_{SI}			960	MHz		1
Noise figure	N_{SI}	7.5	8	9.5	dB	DSB-noise, $f_C = 900$ MHz	1
	N_{SI}	9.5	10	11.5	dB	SSB-noise, $f_C = 900$ MHz including optimum noise matching	

Output of First Mixer MO/ $\bar{M}$ O (open collector)

Output resistance	R_{MO}	11.2	16	20.8	k Ω	$f_{MO} = 45$ MHz	2c
	R_{MO}	7	10	13	k Ω	$f_{MO} = 71$ MHz	2c
Output capacitance	C_{MO}	0.7	1	1.3	pF	parallel to R_{MO}	2c
Total output current	$I_{MO + \bar{M}O}$	3.5	5	6.5	mA		1
Power gain from Signal input	G_{MO}		13	14	dB		1
Intermediate frequency	f_{IF}	35		100	MHz		1

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AC/DC-Characteristics (cont'd)

Parameter	Symbol	Limit Values			Unit	Test Condition	Test Circuit
		min.	typ.	max.			

Input of First Mixer Local Oscillator LO1/LO1

Input resistance	R_{LO1}	490	700	910	Ω	$f_{LO1} = 900 \text{ MHz}$	2a
Input capacitance	C_{LO1}	0.7	1	1.3	pF	parallel to R_{LO1}	2a
Input level	P_{LO1}	-11		3	dBm	see diagram 1	1
	V_{LO1}	178		890	mVpp		1
Input frequency	f_{LO1}			1100	MHz		1

Isolation of First Mixer

From SI to MO	A_{SI-MO}	30			dB	$f_{SI} = 945 \text{ MHz};$ $f_{LO1} = 900 \text{ MHz}$	1
SI to LO1	A_{SI-LO1}	60			dB	$f_{SI} = 945 \text{ MHz};$ $f_{LO1} = 900 \text{ MHz}$	1
LO1 to MO	A_{LO1-MO}	50			dB	$f_{SI} = 945 \text{ MHz};$ $f_{LO1} = 900 \text{ MHz}$	1
LO1 to SI	A_{LO1-SI}	60			dB	$f_{SI} = 945 \text{ MHz};$ $f_{LO1} = 900 \text{ MHz}$	1
MO to SI	A_{MO-SI}	50			dB	$f_{SI} = 945 \text{ MHz};$ $f_{LO1} = 900 \text{ MHz}$	1
MO to LO1	A_{MO-LO1}	65			dB	$f_{SI} = 945 \text{ MHz};$ $f_{LO1} = 900 \text{ MHz}$	1

IF Input IF/IF1

Input resistance	R_{IF1}	63	90	117	Ω		2a
Input capacitance	C_{IF1}	0.35	0.5	0.65	pF	parallel to R_{IF1}	2a
Max. input level	P_{IF1}		-17		dBm	$V_{GC} = 2 \text{ V}, 1 \text{ dB compr. at SO; see diagram 4}$	1
	V_{IF1}		89		mVpp		1
Input intercept point	P_{IP1}	see diagram 5					1
Input frequency	f_{SI}	35		100	MHz		1
Noise figure	N_{SI}	10	11	14	dB	SSB-noise	1

Input for Second Local Oscillator LO2 (VCO external)

Input resistance	R_{LO2}	1.9	2.4	3.1	k Ω	$f_{LO2} = 180 \text{ MHz}$	2b
		1.3	1.8	2.3	k Ω	$f_{LO2} = 360 \text{ MHz}$	2b

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AC/DC-Characteristics (cont'd)

Parameter	Symbol	Limit Values			Unit	Test Condition	Test Circuit
		min.	typ.	max.			
Input capacitance	C_{LO2}	0.7	1	1.3	pF		2b
Input level	P_{LO2}	-20		0	dBm	into 50 Ω	1.1
	V_{LO2}	63		630	mVpp		1.1
Input frequency	f_{LO2}	140		400	MHz		1.1

Voltage Controlled Oscillator VCO (LO2)

VCO-frequency	f_{VCO}	120		250	MHz	with ext. capacitors	1.2
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VCO Output LO2O

Output resistance	R_{LO2O}	0.9	1.2	1.5	k Ω		
Output capacitance	C_{LO2O}	0.7	1	1.3	pF		
Output level	V_{LO2O}	150	160		mVpp	IF $\leq$ 75 MHz	1
		120	140		mVpp	IF $\geq$ 75 MHz	1
Output frequency	f_{LO2O}	15		50	MHz		1

Signal Outputs SOI/ $\overline{SOI}$, SOQ/ $\overline{SOQ}$

Output resistance	R_{SO}	175	250	325	Ω		
Output capacitance	C_{SO}	0.7	1	1.3	pF		
SO frequency roll off	f_{SO}		13.5		MHz	see diagram 6	
DC output level	V_{SO}	2.0		2.5	V		1
Diff. output offset voltage	$V_{SO/\overline{SO}}$			28	mV	between $I/\overline{I}$ or $Q/\overline{Q}$	1
Voltage gain from IF to I/Q-output	G_{SO}	57	61	65	dB	$V_{GC} = 0$ V	1
		-25	-21	-17	dB	$V_{GC} = 2$ V	

Gain Control Input GC

GC-input voltage	V_{GC}	0		2	V		1
GC-input current	$-I_{GC}$			1	μ A	0 V $\leq V_{GC} \leq 2$ V	1
Gain control factor	F_{GC}		40		dB/V	$F_{GC} = dG_{SO}/dV_{GC}$ see diagram 3	1

AC/DC-Characteristics (cont'd)

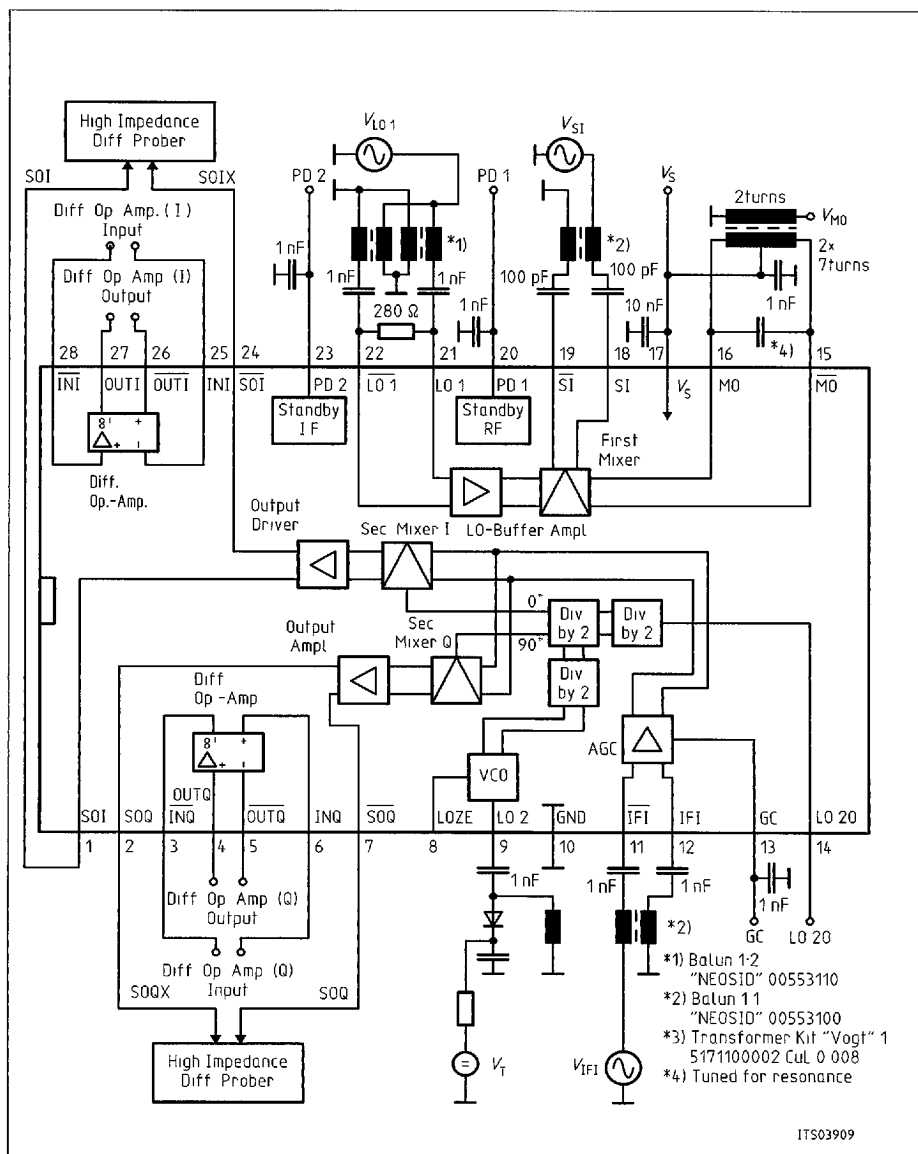
Parameter	Symbol	Limit Values			Unit	Test Condition	Test Circuit
		min.	typ.	max.			

Power-Down Inputs PD1, PD2

L-PD input voltage	V_{PDL}	0		1	V		1
L-PD input current	I_{PD1L} I_{PD2L}			0.1 0.2	μA μA	$0 \leq V_{PD1, 2L} \leq 1 V$	1
H-PD input voltage	V_{PDH}	4		V_S	V		1
H-PD input current	I_{PDH}			10	μA	$4 \leq V_{PD1, 2L} \leq V_S$	1

Differential Operational Amplifier (open loop)

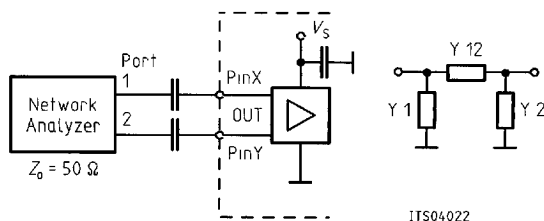
Slew rate	SR		4.6		V/ μs		1
Gain Bandwidth Prod.	GBW		12		MHz		1
Voltage gain	A_{Vo}		55		dB		1
Phase margin	Φ_R		60		degr.		1
Gain margin	A_R		14		dB		1
Common mode Rejection Ratio	$CMRR$		58		dB		1
Offset voltage	V_{OFF}		1		mV		1
Output voltage	V_{OUT}	0.8		$V_S - 1$	V		1



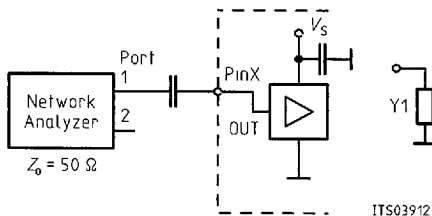
Test Circuit 1

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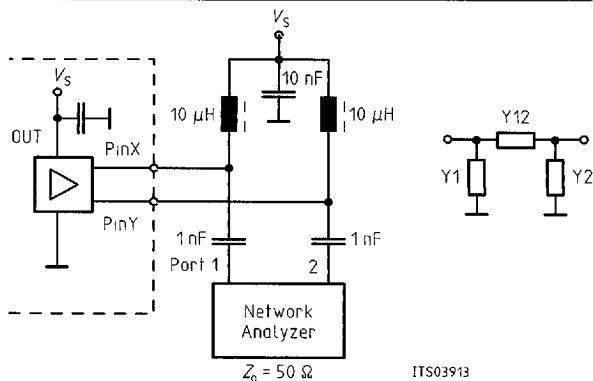
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Test Circuit 2a



Test Circuit 2b

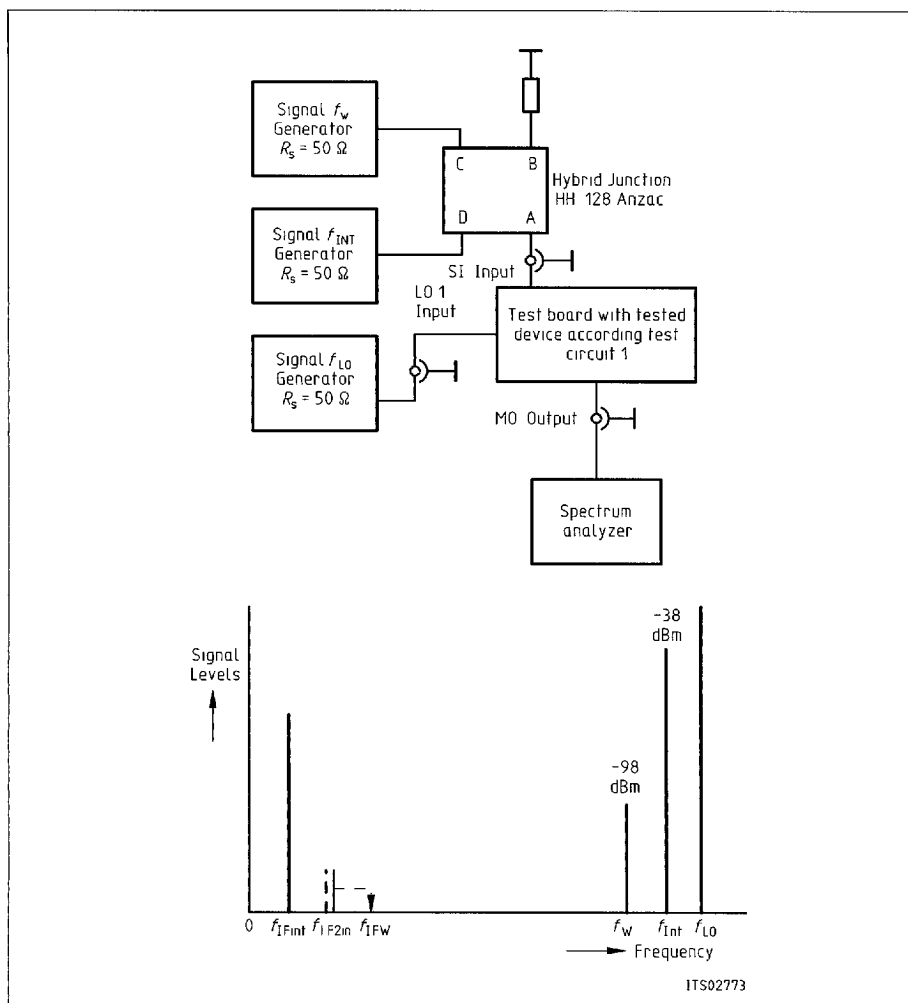


Test Circuit 2c

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The S-parameters are tested at the indicated frequency and the equivalent parallel or series circuit is calculated on this base.

Test Point	Test Circuit	Test Frequency / MHz	Pin x	Pin y
LO1-input impedance	2a	900	21	22
SI-input impedance	2a	900	18	19
IFI-input impedance	2a	45 ... 90	11	12
LO2-input impedance	2b	180, 360	9	—
MO-output impedance	2c	45, 71	15	16



Test Circuit 3

f_W = wanted input signal from received channel

f_{int} = unwanted interfering signal within band : $f_{int} = f_{LO} - f_{IF} / 2$

f_{LO} = local oscillator signal

f_{IFW} = wanted IF signal from received channel : $f_{IFW} = f_{LO} - f_W$

f_{IF1t} = unwanted IF / 2 signal from interfering channel : $f_{IF1t} = f_{LO} - f_{int}$

f_{IF2n} = unwanted harmonic signal of f_{IF2n} : $f_{IF2n} = 2 \times f_{IF1t}$

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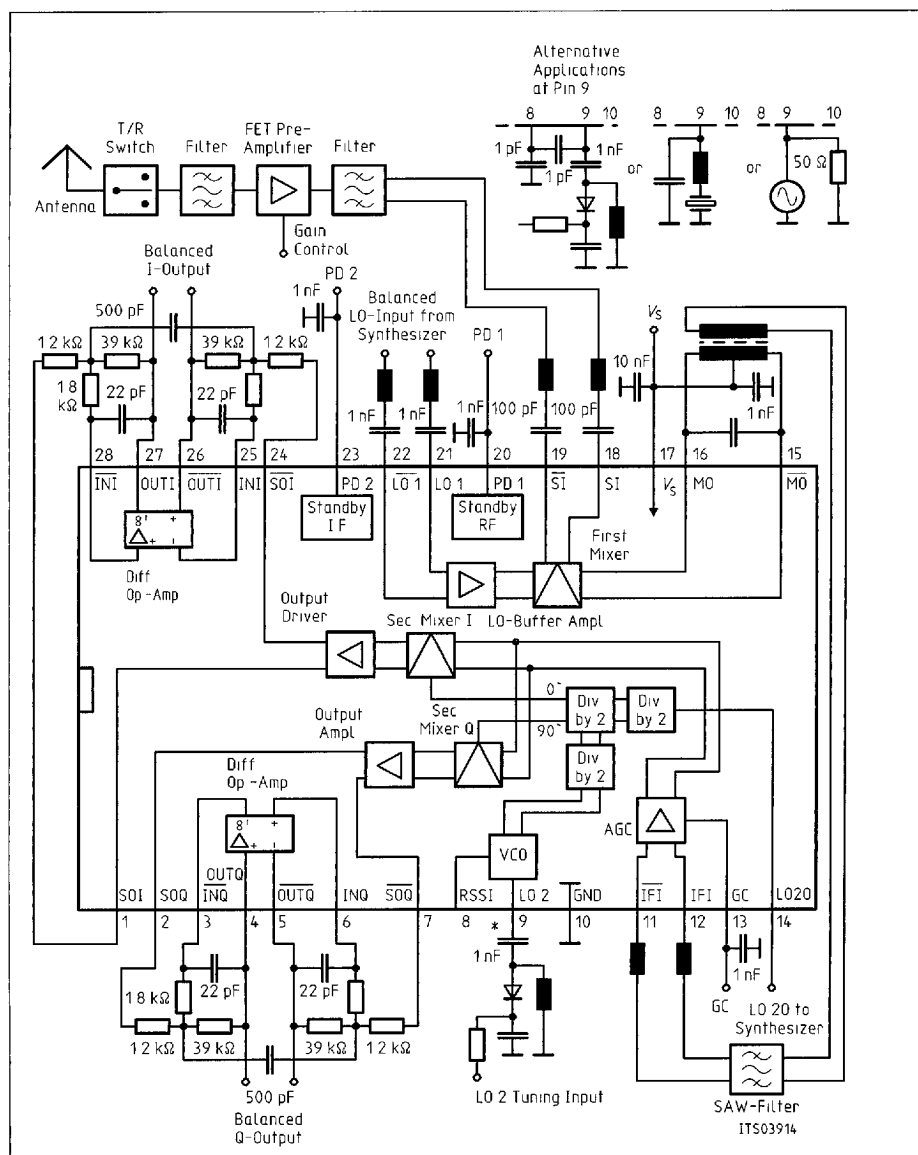
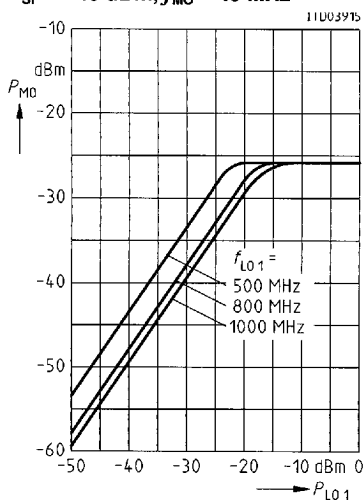
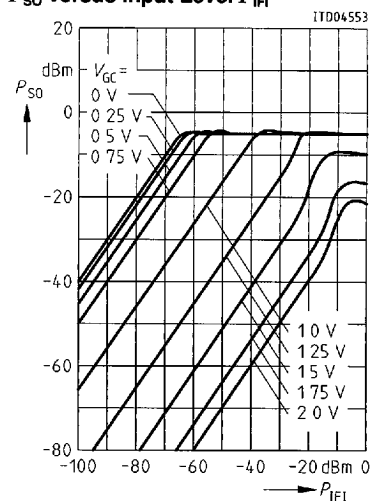


Diagram 1

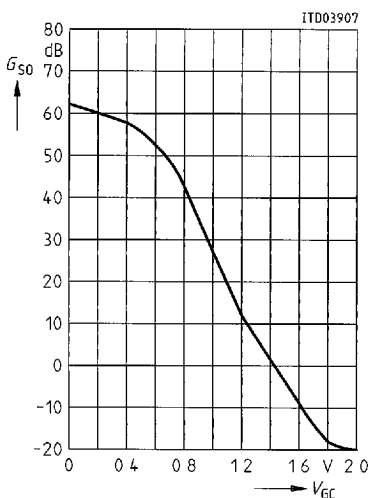
First Mixer Gain versus LO-Level P_{LO1}
 $P_{SI} = -40 \text{ dBm}$, $f_{MO} = 45 \text{ MHz}$

**Diagram 2**

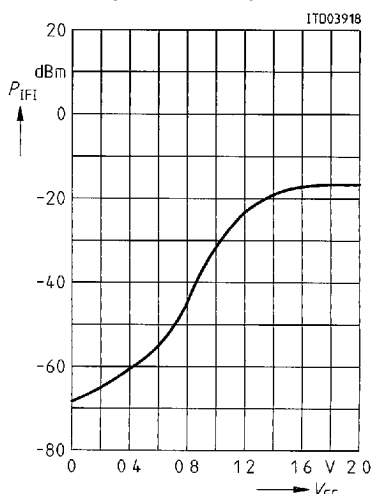
Gain Control Characteristic Output Level P_{SO} versus input Level P_{IFI}

**Diagram 3**

Gain Control Characteristic Voltage Gain G_{SO} versus GC-Voltage V_{GC}

**Diagram 4**

**Gain Control Characteristic Max. Input Level P_{IFI} versus GC-Voltage V_{GC} :
 (1 dB Compression at SO)**



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Diagram 5
Gain-Control Characteristic Input Intercept
Point P_{IPI} versus GC-Voltage V_{GC}

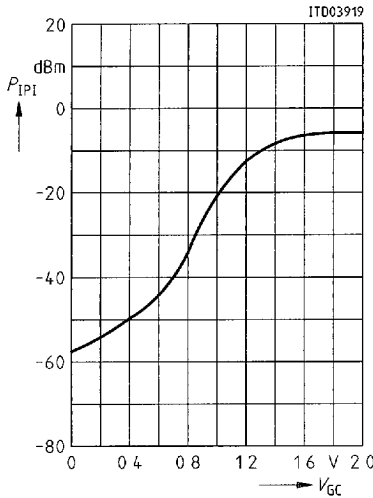
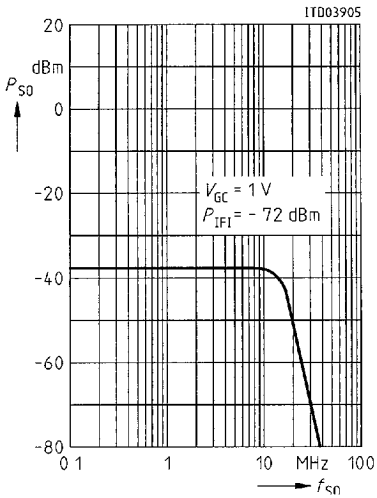
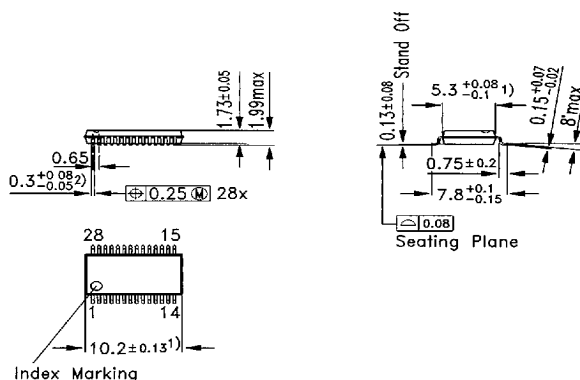


Diagram 6
Frequency Transfer Characteristic of
Outputs SOI / SOQ



Package Outlines

Plastic Package, P-DSO-28-4 (Shrink) (SMD)
(Dual-Small-Outlines)

- 1) Does not include plastic or metal protrusions of 0.15 max per side
- 2) Does not include dambar protrusion of 0.08 max per side

Sorts of Packing

Package outlines for tubes, trays ect. are contained in our
Data Book "Package Information"

SMD = Surface Mounted Device

Dimensions in mm

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B115-H6703-
61-X-7600